General Purpose Transistor

NPN Silicon

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	200	mAdc
Collector Current - Peak (Note 3)	I _{CM}	900	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

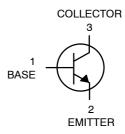
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1AM = Specific Device Code

M = Date Code* ■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]		
MMBT3904LT1G SMMBT3904LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel		
MMBT3904LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel		

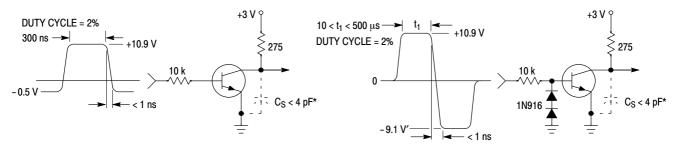
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Chara	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector - Emitter Breakdown Voltage (Id	V _{(BR)CEO}	40	-	Vdc		
Collector - Base Breakdown Voltage (I _C :	= 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc	
Emitter – Base Breakdown Voltage (I _E =	10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	_	Vdc	
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB}	= 3.0 Vdc)	I _{BL}	_	50	nAdc	
Collector Cutoff Current (V _{CE} = 30 Vdc,	V _{EB} = 3.0 Vdc)	I _{CEX}	_	50	nAdc	
ON CHARACTERISTICS (Note 4)		•			•	
$\begin{array}{l} \text{DC Current Gain} \\ \text{(I}_{C} = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 50 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \end{array}$	H _{FE}	40 70 100 60 30	- 300 - -	-		
	V _{CE(sat)}	- -	0.2 0.3	Vdc		
$\begin{aligned} &\text{Base-Emitter Saturation Voltage} \\ &\text{(I}_{C} = 10 \text{ mAdc, I}_{B} = 1.0 \text{ mAdc)} \\ &\text{(I}_{C} = 50 \text{ mAdc, I}_{B} = 5.0 \text{ mAdc)} \end{aligned}$	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc		
SMALL-SIGNAL CHARACTERISTICS		•	•	•	•	
Current - Gain - Bandwidth Product (I _C =	= 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz	
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E =$	0, f = 1.0 MHz)	C _{obo}	-	4.0	pF	
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0.5 \text{ Vdc}$), f = 1.0 MHz)	C _{ibo}	-	8.0	pF	
Input Impedance ($V_{CE} = 10 \text{ Vdc}, I_{C} = 1.0 \text{ Vdc}$) mAdc, f = 1.0 kHz)	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio (V _{CE} = 10 Vdc,	h _{re}	0.5	8.0	X 10 ⁻⁴		
Small – Signal Current Gain (V _{CE} = 10 Vo	h _{fe} 100 400		400	-		
Output Admittance ($V_{CE} = 10 \text{ Vdc}, I_{C} = 1$	h _{oe}	1.0	40	μmhos		
Noise Figure (V_{CE} = 5.0 Vdc, I_{C} = 100 μ	NF	-	5.0	dB		
SWITCHING CHARACTERISTICS		•	•	•	•	
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc,	t _d	-	35		
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	-	35	ns	
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	-	200	200	
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc}$	t _f	-	50	ns	

^{4.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

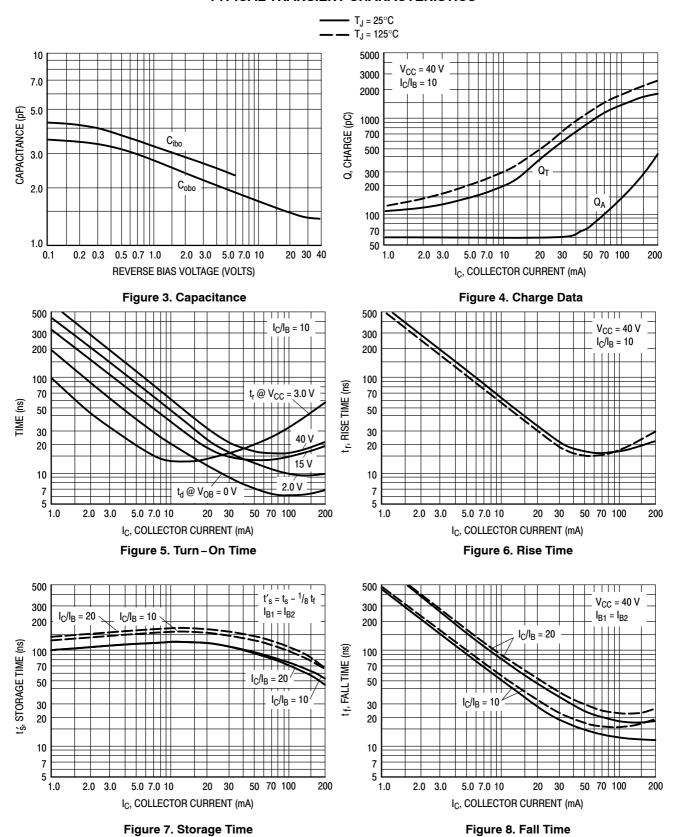


^{*} Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

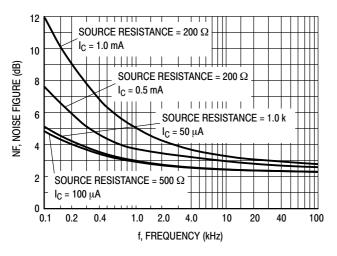
TYPICAL TRANSIENT CHARACTERISTICS



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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



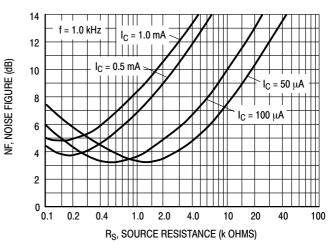
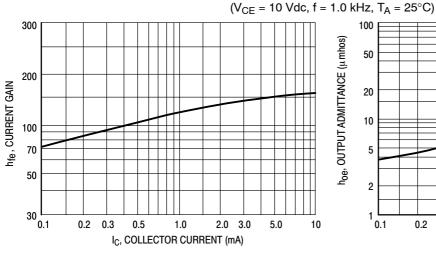


Figure 9.

Figure 10.

h PARAMETERS



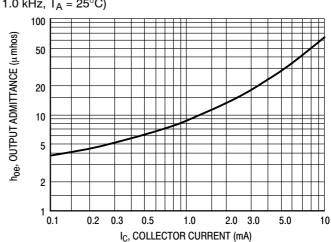
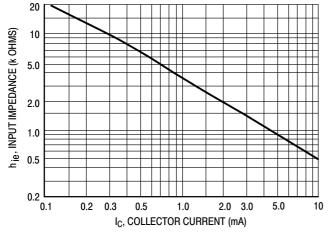
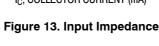


Figure 11. Current Gain

Figure 12. Output Admittance





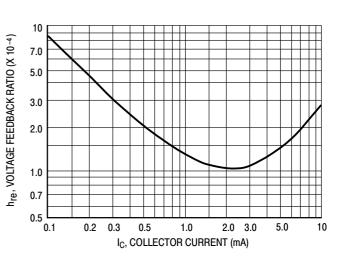


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

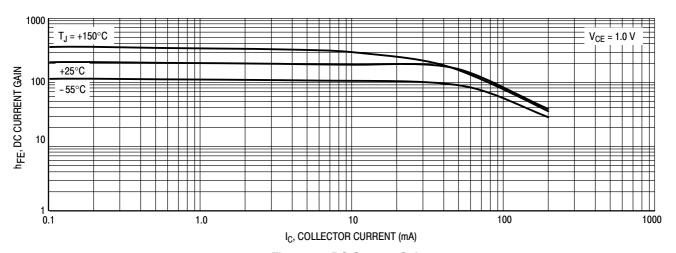


Figure 15. DC Current Gain

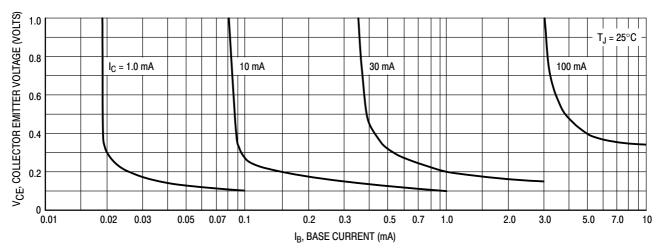


Figure 16. Collector Saturation Region

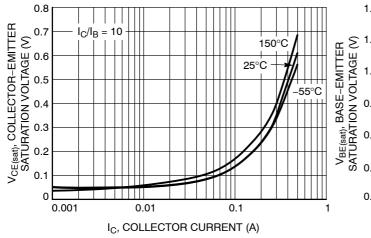


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

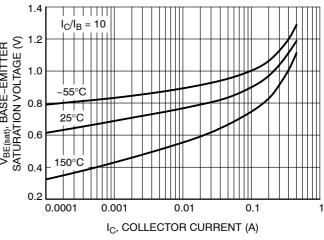


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

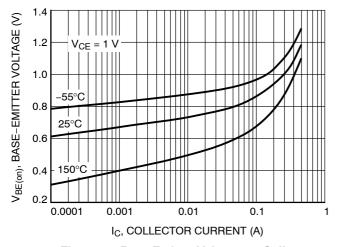


Figure 19. Base Emitter Voltage vs. Collector Current

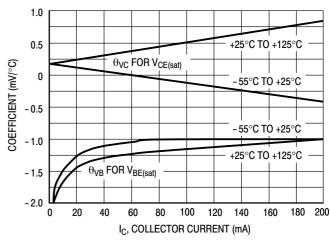


Figure 20. Temperature Coefficients

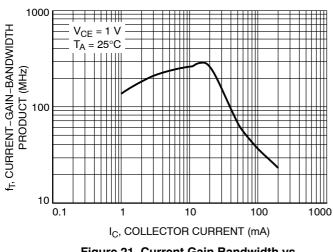


Figure 21. Current Gain Bandwidth vs. Collector Current

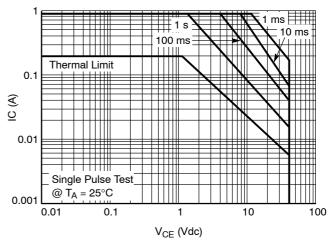
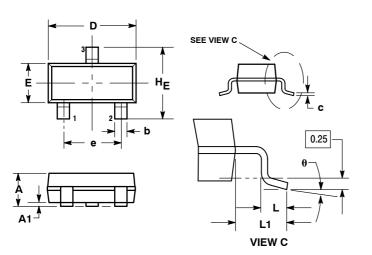


Figure 22. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



NOTES

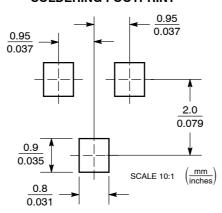
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6:

- PIN 1. BASE 2. EMITT
 - EMITTER
 - COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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